

TOSHIBA

2SB1015A

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

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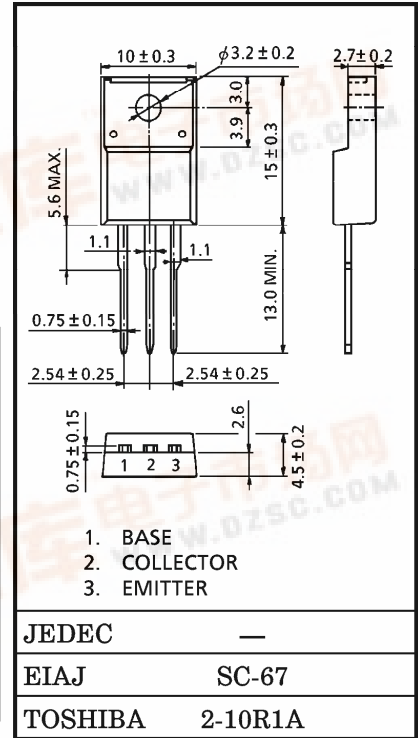
AUDIO FREQUENCY POWER AMPLIFIER APPLICATIONS

Unit in mm

- Low Collector Saturation Voltage : $V_{CE(sat)} = -1.7\text{ V (Max.)}$
($I_C = -3\text{ A}, I_B = -0.3\text{ A}$)
- Collector Power Dissipation : $P_C = 25\text{ W (Tc = 25°C)}$

MAXIMUM RATINGS ($T_a = 25°C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	-60	V
Collector-Emitter Voltage		V_{CEO}	-60	V
Emitter-Base Voltage		V_{EBO}	-7	V
Collector Current		I_C	-3	A
Base Current		I_B	-0.5	A
Collector Power Dissipation	$T_a = 25°C$	P_C	2.0	W
	$T_c = 25°C$		25	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} = -60 V, I _E = 0	—	—	-100	μA
Emitter Cut-off Current		IEBO	V _{EB} = -7 V, I _C = 0	—	—	-100	μA
Collector-Emitter Breakdown Voltage		V _(BR) CEO	I _C = -50 mA, I _B = 0	-60	—	—	V
DC Current Gain		h _{FE} (1) (Note)	V _{CE} = -5 V, I _C = -0.5 A	60	—	200	
		h _{FE} (2)	V _{CE} = -5 V, I _C = -3 A	20	—	—	
Collector-Emitter Saturation Voltage		V _{CE} (sat)	I _C = -3 A, I _B = -0.3 A	—	-0.5	-1.7	V
Base-Emitter Voltage		V _{BE}	V _{CE} = -5 V, I _C = -0.5 A	—	-0.7	-1.0	V
Transition Frequency		f _T	V _{CE} = -5 V, I _C = -0.5 A	—	9	—	MHz
Collector Output Capacitance		C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	—	150	—	pF
Switching Time	Turn-on Time	t _{on}	<p> I_{B1}, I_{B2}, $20 \mu s$, 15Ω, $V_{CC} = -30 V$ INPUT, OUTPUT </p>	—	0.4	—	μs
	Storage Time	t _{stg}		—	1.7	—	
	Fall Time	t _f		$-I_{B1} = I_{B2} = 0.2 A$, DUTY CYCLE $\leq 1\%$	—	0.5	

(Note) : h_{FE}(1) Classification O : 60~120, Y : 100~200

